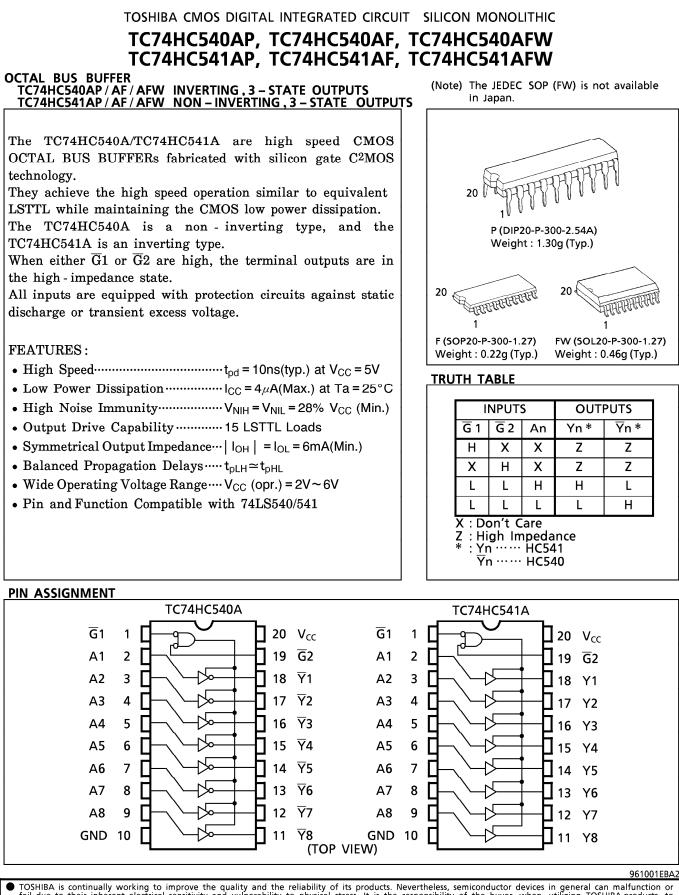
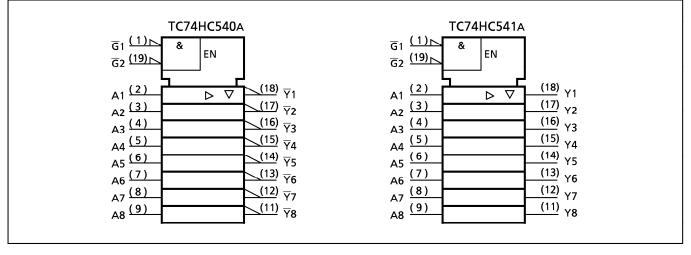
TOSHIBA



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IEC LOGIC SYMBOL



961001EBA2'

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V _{cc}	-0.5~7	V
DC Input Voltage	VIN	-0.5~V _{CC} +0.5	V
DC Output Voltage	V _{OUT}	-0.5~V _{CC} +0.5	V
Input Diode Current	Ι _{ικ}	± 20	mA
Output Diode Current	Ι _{οκ}	±20	mA
DC Output Current	I _{OUT}	± 35	mA
DC V _{cc} /Ground Current	I _{CC}	±75	mA
Power Dissipation	P _D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T _{stg}	-65~150	°C

*500mW in the range of Ta = -40° C~65°C. From Ta=65°C to 85°C a derating factor of -10mW/°C shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V _{cc}	2~6	V
Input Voltage	VIN	0~V _{CC}	V
Output Voltage	V _{OUT}	0~V _{CC}	V
Operating Temperature	T _{opr}	-40~85	°C
Input Rise and Fall Time	t _r , t _f	$\begin{array}{l} 0 \sim 1000 \ (V_{CC} = 2.0V) \\ 0 \sim 500 \ (V_{CC} = 4.5V) \\ 0 \sim 400 \ (V_{CC} = 6.0V) \end{array}$	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL		TEST CONDITION		V _{cc}	Ta = 25°C			Ta = −40~85°C		UNIT
				(V)	MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	VIH				1.50 3.15 4.20			1.50 3.15 4.20		v
Low - Level Input Voltage	VIL			2.0 4.5 6.0			0.50 1.35 1.80		0.50 1.35 1.80	v
High - Level Output Voltage	V _{OH}	V _{IN} =	$I_{OH} = -20\mu A$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0		1.9 4.4 5.9		v
		V_{IH} or V_{IL}	I _{OH} = — 6 mA I _{OH} = — 7.8 mA	4.5 6.0	4.18 5.68	4.31 5.80	_	4.13 5.63	_	
Low - Level Output Voltage V _{OL}	Vol	$V_{\rm OI}$ $V_{\rm IN} =$	I _{OL} = 20μΑ	2.0 4.5 6.0		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	v
	VOL VIH OR VIL	I _{OL} = 6 mA I _{OL} = 7.8mA	4.5 6.0		0.17 0.18	0.26 0.26	-	0.33 0.33		
3 - State Output Off - State Current	I _{oz}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		6.0	_		±0.5	_	± 5.0	
Input Leakage Current	I _{IN}	$V_{1N} = V_{CC} \text{ or } GND$		6.0	_	_	±0.1	—	± 1.0	μΑ
Quiescent Supply Current	I _{cc}	$V_{IN} = V_{CC} \text{ or } GND$		6.0	-	_	4.0	_	40.0	

PARAMETER	SYMBOL	TEST	CL (pF)	Vcc	1	Ta = 25°C		Ta = -40~85°C		UNIT
	STIVIBUL	CONDITION		V _{CC} (V)	MIN.	ΤΥΡ.	MAX.	MIN.	MAX.	
Output Transition Time	t _{TLH}			2.0	—	25	60	—	75	
	t _{THL}		50	4.5 6.0	_	6	12 10	_	15 13	
				2.0	_	36	90		115	
Propagation Delay Time	t _{pLH}		50	4.5	_	12	18	_	23	
				6.0		10	15	—	20	
				2.0	_	51	130	—	165	
	t _{pHL}		150	4.5		17	26	_	33	
				6.0	—	14	22	—	28	-
	t _{pZL}	$R_L = 1k\Omega$	50	2.0	—	45	125	_	155	
				4.5 6.0	_	14 12	25 21	_	31 26	
Output Enable Time	t _{pZH}		150	2.0	_	60	165	_	205	ns
				4.5	_	19	33	_	41	
				6.0	—	16	28	—	35	
Output Disable time	t _{pLZ}	$R_L = 1k\Omega$	50	2.0	_	40	125	—	155	
				4.5	—	16	25	—	31	
	t _{pHZ}			6.0	_	14	21	_	26	
Input Capacitance	CIN				_	5	10	—	10	
Output Capacitance	COUT					10	—		—	pF
Power Dissipation Capacitance		TC74HC540A			32	—	_	_] "'	
	C _{PD} (1)	A			35	—	_	_		

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 6ns$)

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

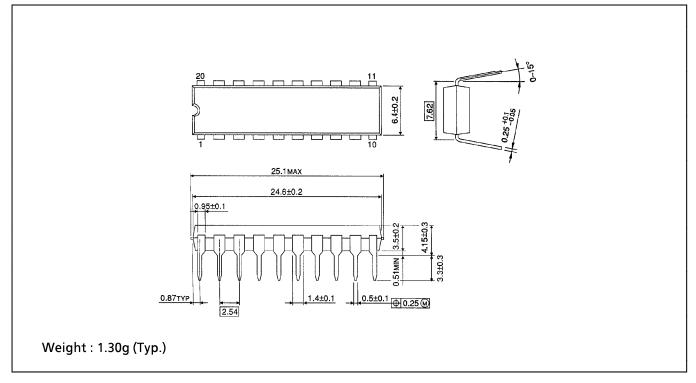
Average operating current can be obtained by the equation:

 \vec{I}_{CC} (opr) = $C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 8$ (per bit)

DIP 20PIN OUTLINE DRAWING (DIP20-P-300-2.54A)



Unit in mm



SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

